



PATENT APPLICATION DFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Attn: OIPE

Izumi FUSEGAWA et al.

Group Art Unit: 1722

Application No.: 10/510,695

Docket No.: 121356

Filed: October 8, 2004

For: METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON
SINGLE CRYSTAL AND SILICON WAFER

SECOND REQUEST FOR CORRECTION OF PALM RECORDS

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Attached is a photocopy of the original filing receipt on which an error has been corrected in red. This error is being brought to the attention of the Patent and Trademark Office so that it may correct its records.

Respectfully submitted,

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Date: July 25, 2006

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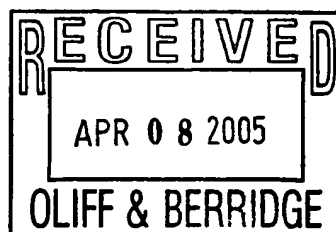


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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/510,695	10/08/2004	1765	950	121356	3	9	3

25944
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CONFIRMATION NO. 3939
 FILING RECEIPT



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Assignment For Published Patent Application

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Power of Attorney: The patent practitioners associated with Customer Number 25944.

Domestic Priority data as claimed by applicant

This application is a 371 of PCT/JP03/05167 04/23/2003

Foreign Applications

JAPAN 2002-122250 04/24/2002

Projected Publication Date: 07/07/2005**Non-Publication Request:** No**Early Publication Request:** No

Title

~~Method for producing silicon single crystal and silicon single crystal and silicon wafer~~

Preliminary Class

117

METHOD OF MANUFACTURING SILICON SINGLE
CRYSTAL, SILICON SINGLE CRYSTAL AND
SILICON WAFER

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